Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	2	34	50	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1,3	1.55	V
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	1000	4000	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 25 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; gate open circuit; Fig. 12	-	44	-	A/ms

## 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		T2—T1
3	G	gate		G G
mb	T2	mounting base; main terminal 2		sym051

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA225B-600B	TO263	BTA225B-600B,118	Reel	800	TO263E	26-May-2017

# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 91 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	25	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig 4; Fig 5	-	190	А
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	209	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN	-	180	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 100 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
$P_GM$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

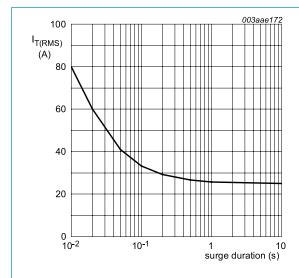


Fig. 1. RMS on-state current as a function of surge duration; maximum values

 $f = 50 Hz; T_{mb} = 91 °C$ 

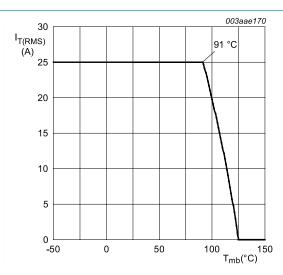


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

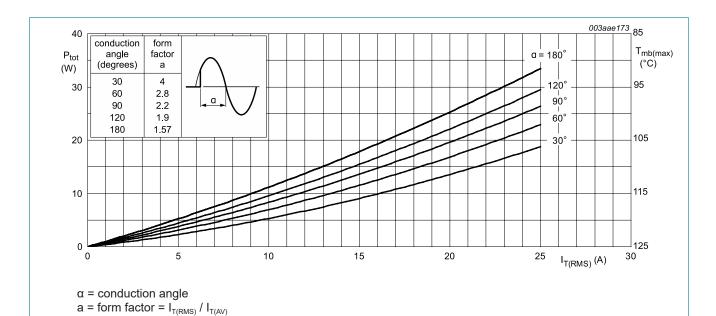


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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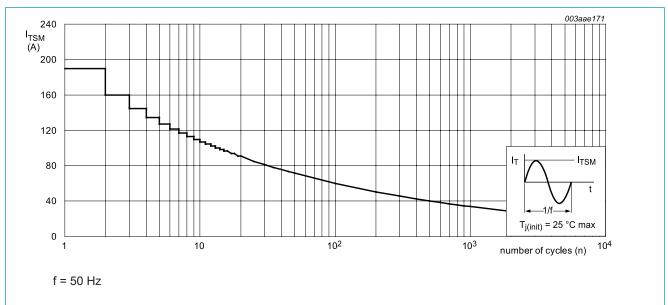


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	full cycle; Fig. 6	-	-	1	K/W
	from junction to mounting base	half cycle; <u>Fig. 6</u>	-	-	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	55	-	K/W

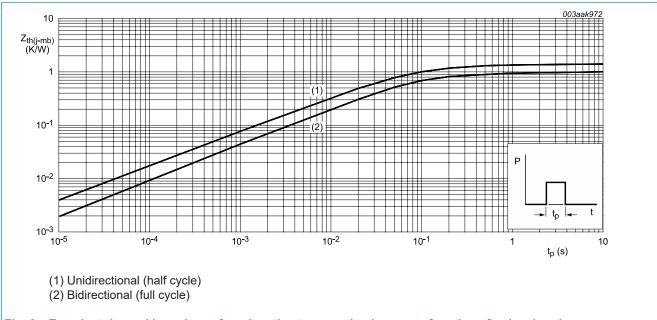


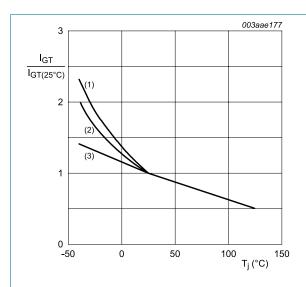
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 9. Characteristics

### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;  T_j = 25 °C; Fig. 7$	2	18	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	21	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	2	34	50	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+; T_j = 25 °C; Fig. 8$	-	31	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	34	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	30	60	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	31	60	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1,3	1.55	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics			'	'	
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	1000	4000	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 25 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; gate open circuit; Fig. 12	-	44	-	A/ms

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- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

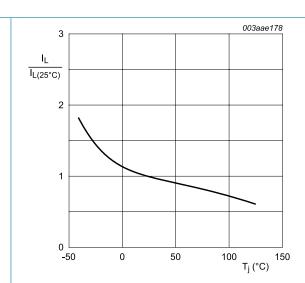


Fig. 8. Normalized holding current as a function of junction temperature

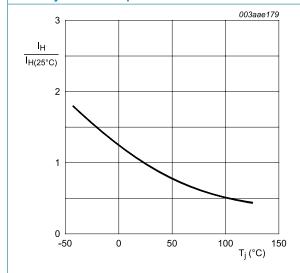
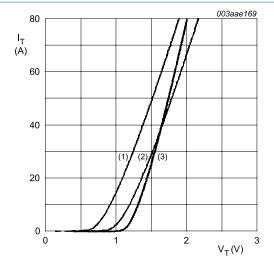


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o$  = 1.073 V;  $R_s$  = 0.015 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

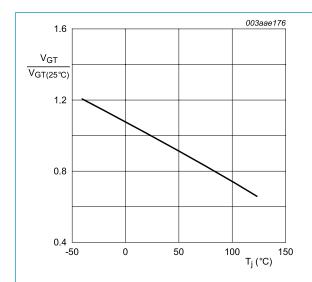


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

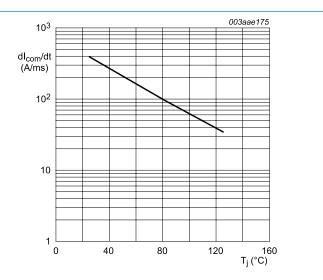
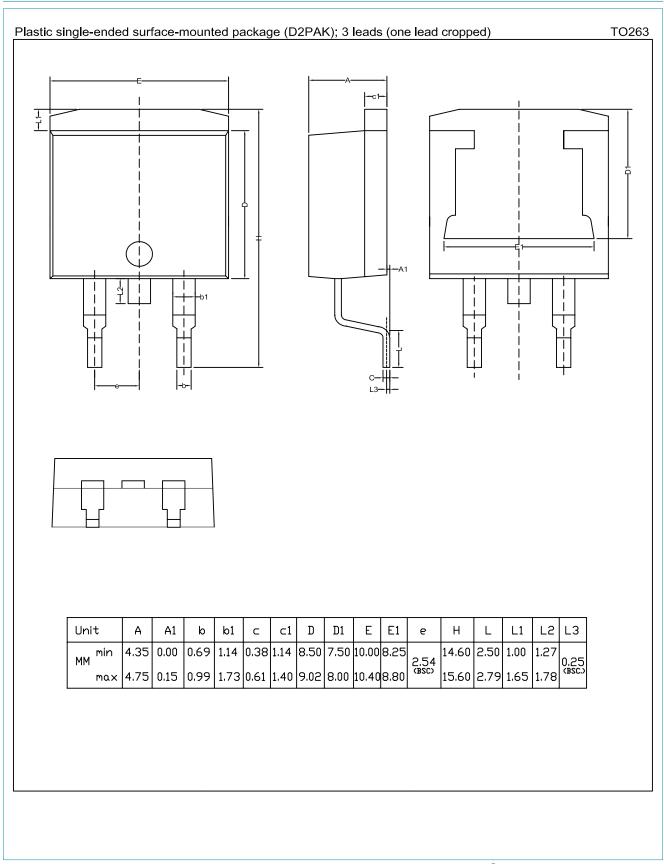


Fig. 12. Critical rate of change of commutating current as a function of junction temperature; typical values

# 10. Package outline



### 11. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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